



Surface Mount Microwave Schottky Mixer Diodes

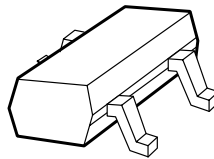
Technical Data

HSMS-8101 Single
HSMS-8202 Series Pair
HSMS-8207 Ring Quad
HSMS-8209 Crossover Quad

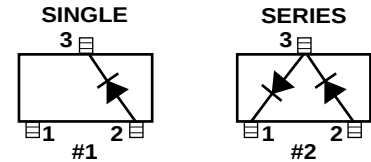
Features

- Optimized for use at 10-14 GHz
- Low Capacitance
- Low Conversion Loss
- Low RD
- Low Cost Surface Mount Plastic Package

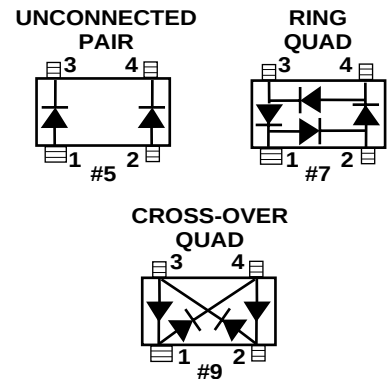
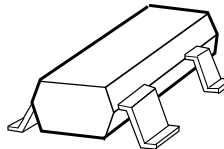
Plastic SOT-23 Package



Package Lead Code Identification (Top View)



Plastic SOT-143 Package



Description/Applications

These low cost microwave Schottky diodes are specifically designed for use at X/Ku-bands and are ideal for DBS and VSAT downconverter applications. They are available in SOT-23 and SOT-143 standard package configurations.

Note that Agilent's manufacturing techniques assure that dice found in pairs and quads are taken from adjacent sites on the wafer, assuring the highest degree of match.

Absolute Maximum Ratings^[1], $T_A = +25^\circ\text{C}$

Symbol	Parameter	Unit	Min.	Max.
P_T	Total Device Dissipation ^[2]	mW	—	75
P_{IV}	Peak Inverse Voltage	V	—	4
T_J	Junction Temperature	$^\circ\text{C}$	—	+150
T_{STG}, T_{op}	Storage and Operating Temperature	$^\circ\text{C}$	-65	+150

Notes:

1. Operation in excess of any one of these conditions may result in permanent damage to the device.
2. Measured in an infinite heat sink at $T_{CASE} = 25^\circ\text{C}$. Derate linearly to zero at 150°C per diode.

ESD WARNING:

Handling Precautions Should Be Taken To Avoid Static Discharge.

DC Electrical Specifications, $T_A = 25^\circ\text{C}$

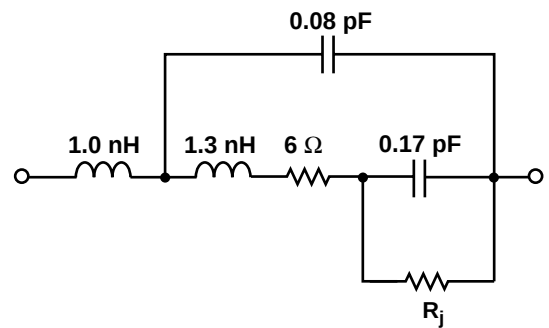
Symbol	Parameters and Test Conditions	Units	HSMS-8101		HSMS-8202		HSMS-8207		HSMS-8209	
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.
V_{BR}	Breakdown Voltage $I_R = 10\ \mu\text{A}$	V	4		4		4		4	
C_T	Total Capacitance $V_R = 0\ \text{V}$, $f = 1\ \text{MHz}$	pF		0.26		0.26		0.26		0.26
ΔC_T	Capacitance Difference $V_R = 0\ \text{V}$, $f = 1\ \text{MHz}$	pF		—		0.04		0.04		0.04
R_D	Dynamic Resistance $I_F = 5\ \text{mA}$	Ω		14		14		14		14
ΔR_D	Dynamic Resistance Difference $I_F = 5\ \text{mA}$	Ω		—		2		2		2
V_F	Forward Voltage $I_F = 1\ \text{mA}$	mV	250	350	250	350	250	350	250	350
ΔV_F	Forward Voltage Difference $I_F = 1\ \text{mA}$	mV		—		20		20		20
Lead Code			1		2		7		9	
Package Marking Code in White			R1		R2		R7		R9	

RF Electrical Parameters, $T_A = 25^\circ\text{C}$

Symbol	Parameter	Units	Typical
L_c	Conversion Loss at 12 GHz	dB	6.3
Z_{IF}	IF Impedance	Ω	150
SWR	SWR at 12 GHz		1.2

Note:DC Load Resistance = $0\ \Omega$; LO Power = 1 mW.**SPICE Parameters**

$I_S = 4.6\ \text{E-}8$	$E_G = 0.69$	TT = 0
$R_S = 6$	$C_{JO} = 0.18\ \text{E-}12$	
$N = 1.09$	$P_B (V_J) = 0.5$	
$B_V = 7.3$	$M = 0.5$	
$I_{BV} = 10\text{E-}5$	$FC = 0.5$	

Linear Equivalent Circuit**Self Bias**

	1 mA	2.5 mA
R_j	263	142

Typical Performance, $T_C = 25^\circ\text{C}$

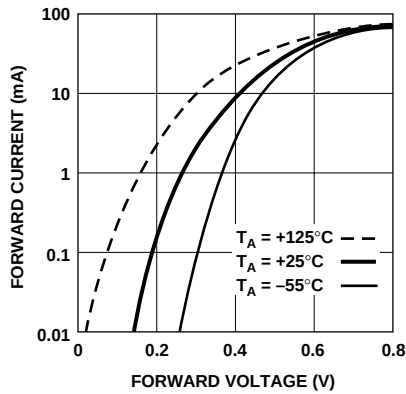


Figure 1. Typical Forward Current vs. Forward Voltage at Three Temperatures.

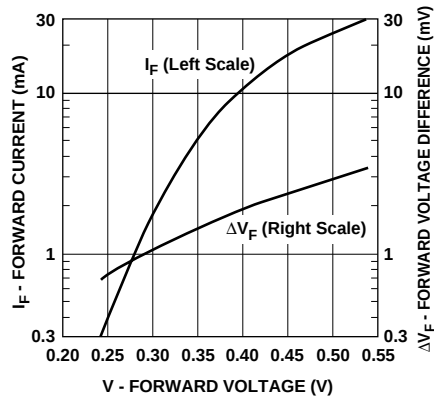


Figure 2. Typical VF Match, HSMS-820X Pairs and Quads.

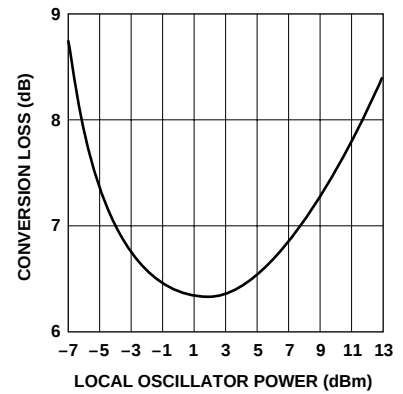


Figure 3. Typical Conversion Loss vs. Local Oscillator Power.

Ordering Information

Specify part number followed by option. For example:

HSMS - 8101 - XXX

_____ Bulk or Tape and Reel Option

_____ Part Number

_____ Surface Mount Schottky

Profile Option Descriptions

- BLK = Bulk
- TR1 = 3K pc. Tape and Reel, Device Orientation Figures 4, 5
- TR2 = 10K pc. Tape and Reel, Device Orientation Figures 4, 5

Tape and Reeling conforms to Electronic Industries RS-481, "Taping of Surface Mounted Components for Automated Placement."

Device Orientation

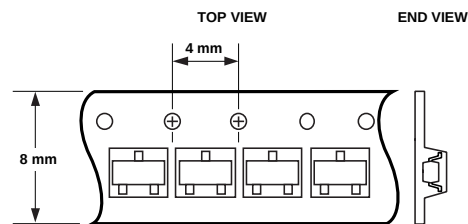
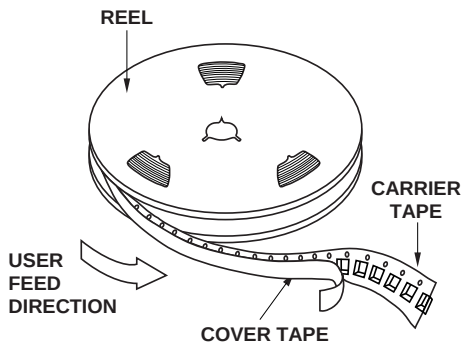


Figure 4. Option -TR1/-TR2 for SOT-23 Packages.

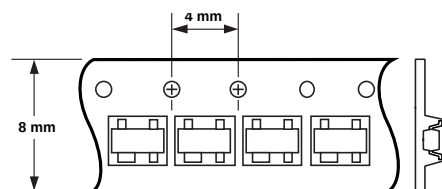


Figure 5. Option -TR1/-TR2 for SOT-143 Packages.



Lead Material	Alloy 42
Lead Finish	Tin-Lead 85-15%
Maximum Soldering Temperature	260°C for 5 seconds
Minimum Lead Strength	2 pounds pull
Typical Package Inductance	2 nH
Typical Package Capacitance	0.08 pF (opposite leads)

DIMENSIONS ARE IN MILLIMETERS (INCHES)

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5968-3886E (2/00)